Suppressing Al Memory-Effect on CVD growth of 4H-SiC Epilayers by adding Hydrogen Chloride Gas

Shiyang Ji1, Kazutoshi Kojima1, Yuuki Ishida1, Shingo Saito1, Sadafumi Yoshida1, Hidekazu Tsuchida2, Hajime Okumura1

1 Advanced Power Electronics Research Center (ADPERC), National Institute of Adv. Ind. Sci. and Tech. (AIST) Umezono 1-1-1, Tsukuba, Ibaraki 305-8568, Japan Phone: +81-29-861-8495 E-mail: aist-ki@aist.go.jp
2 Central Research Institute of Electric Power Industry (CRIEPI) 2-6-1 Nagasaki, Yokosuka, Kanagawa 240-0196, Japan

Abstract

By using site-competition growth with the assistance of HCl gas, Al memory-effect on CVD growth of 4H-SiC was suppressed to an extremely low level. Al concentration differences more than five orders of magnitude were obtained, e.g., steep change from 10^{29} to 10^{14} cm^{-3}.

1. Introduction

The 4H polytype of silicon carbide (SiC) material is very competitive to Si in application fields of high power/frequency devices. The chemical vapor deposition (CVD) was widely used to fabricate SiC device structures. However, an intrinsic problem exists that, in p-type 4H-SiC growth, the memory-effect is strong: the former growth run acting as an additional doping source. The severe case is the unpredictable change of conductivity type [1]. Since it has been reported that devices formed by a continual multilayer growth demonstrate superior performance than that by an interrupted growth [2], we has studied the methods using site competition growth to realize a continual growth of p/n epilayers in the same reactor [3]. The reduction factor (the ratio of Al concentration N_A in p layer and that in the following undoped layer) of about 1/17,000 has been achieved, e.g., N_A from 9×10^{19} to 6×10^{15} cm^{-3} or from 1.7×10^{20} to 1.0×10^{16} cm^{-3}. While, La Via et al. reported the growth using trichlorosilane can suppress Al-impurity level to 10^{14} cm^{-3} after a p layer growth of N_A=1×10^{15} cm^{-3}[4], but it causes an up-limit of Al doping level around 10^{18} cm^{-3}. Nordell et al. tried to suppress unintentional Al doping by using HCl flushing combined with varying C/Si ratios [5]. Abrupt Al distributions (N_A at surface layers 10^{19} to 2×10^{15} cm^{-3}; inner layers 1.5×10^{16} to 7×10^{15} cm^{-3}) have been obtained. However, Al-impurity level around mid of 10^{15} cm^{-3} are thought insufficient for fabricating insulated gate bipolar transistor (IGBT) multilayer structures [6], where it grows an n-type field stopper layer (1×10^{17} cm^{-3}) right after a p' layer. The precise control of n-type doping in field stopper layer seems requiring a further reduction of Al-impurity level below 10^{15} cm^{-3}.

To form the succeeding layer with extremely low Al-impurity level (~10^{15} cm^{-3}) right after the growth of heavily Al-doped layer (~10^{20} cm^{-3}), this work was carried out basing on the previous findings [2, 5]. In addition, HCl gas was introduced into the CVD growth process as well as using site competition growth, and the related HCl inletting effect was investigated and discussed.

2. Experimental and Results

Experimental

A horizontal hot-wall CVD system equipped with standard precursors and gases, SiH_{4}, C_{3}H_{8}, trimethylaluminium (TMA) and dilute HCl (10% in H_{2}), was employed. On as-received n-type 8° off-oriented 4H-SiC wafers, the growth was carried out at the pressure of 10 kPa and the temperature of 1620°C. H_{2} was used as the carrier gas and constantly supplied at 80 slm for all growth. TMA and SiH_{4} flow rates were set at 40 and 30 sccm, respectively, while C_{3}H_{8} flow rate was varied in the range of 4–10 sccm in C:Si mole ratios of 0.4–1. Secondary ion mass spectrometry (SIMS) was used to obtain Al-impurity concentrations.

Results

Figure 1 shows N_A profiles of the interfaced area around samples consisting of an Al-doped and an undoped epilayers grown at C/Si=1 (a) without and (b),(c) with HCl flushing at various dilute HCl flow rates. Between the growth of heavily Al-doped layer and that of undoped layer, 1 minute interruption of source gas flows (only H_{2} flow) was inserted. In the case without HCl flushing, the reduction factor defined by dividing N_A of undoped layer by that of doped one is found about 1/50 as shown in Fig.1(a). Introducing a 5 min HCl flushing reduces N_A in the undoped layer as seen in Fig. 1(b) and (c). The figure indicates that HCl flushing procedure effectively remove Al species probably absorbed on reactor wall. However, a slow decreasing of N_A with growth is seen in Fig. 1(c). Figure 2 shows the HCl flow rate dependence of the reduction factor, which reveals a saturation of Al suppression effect with the increase of HCl flow rate. From these results, in the growth stage of undoped layer, the main source of Al impurities is considered to be decomposition or H_{2} etching of Al-SiC alloy deposited on reactor parts during the growth of heavily doped layer, and therefore, it is hard to diminish due to concurrent H_{2} etching after HCl flushing. To reduce
Al-impurity level by hindering Al atoms incorporation further, site competition growth (Si-rich) as well as adding HCl in the growth was performed. In this experiment, the growth was done at C/Si=0.4–0.8. Figures 3(a) and (b) show $N_{Al}$ profiles of samples grown with HCl flushing at C/Si=0.4, where dilute HCl flow rates are 200 sccm and 2 slm, respectively. Noting that, to minimize the influence of remaining HCl in reactor, after HCl flushing, a 5 min waiting (only H2) has been performed. Comparing with the results in Fig. 1, the figures reveal the decrease in $N_{Al}$ about one order to $10^{16} \text{ cm}^{-3}$. Figures 3(c) and (d) show the $N_{Al}$ profiles of samples grown by introducing HCl during growth, instead of HCl flushing procedure, where the dilute HCl flow rates are 200 sccm and 2 slm, respectively. After the growth of Al-doped layer, a 1 min interval of ceasing all source gases flow (only H2 in) was inserted. The figures show the reduction of $N_{Al}$ in undoped epilayer down to the order of $10^{14} \text{ cm}^{-3}$, which suggests that HCl inletting during the growth efficiently hinder Al incorporation at low C/Si ratio, which brings about an additional one order reduction of Al-impurity level. The relations between the reduction factor and the C/Si ratios for various HCl inletting conditions are summarized in Fig.4. The reduction factor $\sim1/105,000$ was attained by adding 2 slm dilute HCl during the growth of undoped layer at C/Si=0.4.

3. Conclusions

The suppression of Al memory-effect in growing 4H-SiC by hot-wall CVD was investigated. The site competition growth combined with adding HCl gas successfully suppresses Al memory-effect, and a five order reduction in $N_{Al}$ has been achieved, e.g., from $N_{Al}$$\sim$$10^{20} \text{ cm}^{-3}$ in a heavily Al-doped layer to $10^{14} \text{ cm}^{-3}$ in an undoped one. The achieved results are thought valuable to devices involving heavily Al-doped layers. Detailed characterizations and the growth will be reported on the conference.

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References